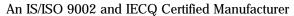


Continental Device India Limited







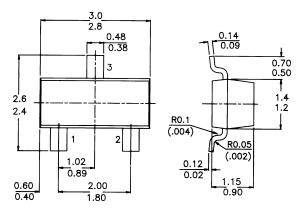
SOT-23 Formed SMD Package

CMBT2369

SILICON PLANAR EPITAXIAL SWITCHING TRANSISTOR

N-P N transistor

Marking CMBT2369 = IJ PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm



Pin configuration

- 1 = BASE
- 2 = EMITTER 3 = COLLECTOR
- 1

ABSOLUTE MAXIMUM RATINGS

I DOCECTE IVE EMINEUT IN THE VOIC			
Collector-base voltage (open emitter)	V_{CB0}	max.	40 V
Collector-emitter voltage ($V_{BE} = 0$)	$V_{C\!E\!S}$	max.	40 V
Collector-emitter voltage (open base)	V_{CE0}	max.	15 V
Collector current (d.c. value)	I_C	max.	500 mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	250 mW
D.C. current gain			
$I_C = 10mA; V_{CE} = 1 V$	h_{FE}	40 to	o 120
$I_C = 100 \text{ mA}; V_{CE} = 2 \text{ V}$	h_{FE}	>	20
Storage time			
$I_{Con} = I_{Bon} = I_{Boff} = 10 \text{ mA}$	t_{S}	<	13 ns

RATINGS (at $T_A = 25$ °C unless otherwise specified)			
Limiting values			
Collector-base voltage (open emitter)	V_{CB0}	max.	40 V
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	40 V
Collector-emitter voltage (open base)	V_{CE0}	max.	15 V
Emitter-base voltage (open collector)	V_{EB0}	max.	4.5 V
Collector current (d.c. value)	I_C	max.	500 mA
Total power dissipation up to $T_{amb} = 25 ^{\circ}C$	P_{tot}	max.	250 mW
Storage temperature	T_{Stg}	−55 to	150° C
Junction temperature	T_j	max.	150 ° C
THERMAL RESISTANCE			
From junction to ambient in free air	$R_{th\ j-a}$	=	<i>500</i> K/W
CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless otherwise spec	ified)		
$T_i = 25$ °C unless otherwise specified			
Collector cut-off current			
$I_E = 0; \ V_{CB} = 20 \ V$	I_{CB0}	<	400 nA
$I_E = 0; \ V_{CB} = 20V; \ T_i = 125^{\circ}C$	I_{CB0}	<	<i>30</i> m <i>A</i>
Saturation voltages	CDO		
$I_C = 10 \text{ mA}; l_B = 1 \text{ mA}$	V _{CEsat}	<	0,25 V
<i>C</i>	V_{BEsat}		0,85 V
D.C. current gain	DESA	,	,
$I_C = 10mA$; $V_{CE} = 1 V$	h_{FE}	40 to	120
$I_C = 10mA; V_{CE} = 1 V; T_{amb} = -55^{\circ}C$	h_{FE}	>	20
$I_C = 100 \text{ mA}; V_{CE} = 2 \text{ V}$	h_{FE}	>	20
Output capacitance at $f = 1$ MHz	1 L		
$I_E = 0$; $V_{CB} = 5V$	Co	<	4,0 pF
Small-signal current gain			-, - F-
$I_C = 1.0$ mA; $V_{CE} = 10$ V; $f = 100$ MHz; $T_{amb} = 25$ °C	h_{fe}	>	5.0
Breakdown voltages	16		0,0
$I_C = 10 \text{ mA; } I_B = 0$	V _{(BR)CEO}	min.	15 V
$I_C = 10$ mA; $I_E = 0$	V _(BR) CBO	min.	40 V
$I_C = 0$; $I_E = 10$ mA	$V_{(BR)EBO}$	min.	4,5 V
$I_C = 10$ mA; $V_{BE} = 0$	V _{(BR)CES}	min.	40 V
10 Iona 1, V BE	' (BR)CES	111111	10 ,
Switching times at $T_{amb} = 25$ °C			
Storage time		typ.	5,0 ns
$I_{Con} = I_{Bon} = -I_{Boff} = 10 \text{ mA}$	t_S	<	13 ns
Turn-on time	t _{on}	typ.	8,0 ns
$I_C = 10\text{mA}$; $I_{Bon} = 3\text{mA}$; $V_{CC} = 3V$	t _{on}	<i>typ.</i> <	12 ns
Turn-off time $T_{\text{UN}} = S_{\text{UN}}, V_{\text{UN}} = S_{\text{UN}}, V_{\text{UN}} = S_{\text{UN}}$	t _{off}	typ.	10 ns
$I_C = 10\text{mA}$; $I_{Bon} = 3\text{mA}$; $I_{Boff} = 1.5\text{mA}$; $V_{CC} = 3V$		<i>typ.</i> <	18 ns
IC = IOIII - I, IBOII = III - I, IIII - I, IIII - IV	t_{off}	`	10 113

Notes

Disclaimer

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